



2N3055S

NPN Silicon Low Frequency High Power Transistor



Features:

1. Heavy working current.Good temperature stability.Excellent thermal fatigue capability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch,low frequency power amplify,power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications	Test Condition
Collector-Emitter Voltage	V_{CEO}	V	60	
Emitter-Base Voltage	V_{EBO}	V	7	
Max. Collector Current	I_{CM}	A	15	
Max. Collector Dissipation	P_{CM}	W	117	($T_c=25^\circ\text{C}$)
Junction Temperature	T_{jm}	$^\circ\text{C}$	175	
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175	
Collector-Dase Laekage Current	I_{CBO}	mA	Max.:0.7	$V_{CB}=100\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:0.75	$I_c=4\text{A}, I_b=0.4\text{A}$
DC Current Gain	h_{FE}		Min.:20, Max.:70	$V_{CE}= 4\text{V}, I_c= 4\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	60	$I_c=1\text{mA}$
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	7	$I_E=1\text{mA}$

Outline and Dimensions: